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(71) Applicant (*for all designated States except US*): MICRON TECHNOLOGY, INC. [US/US]; 8000 S. Federal Way, Boise, ID 83716 (US).

(72) Inventor: MANNING, Montgomery, H.; 3695 West Houseland Court, Eagle, ID 83616 (US).

(74) Agents: LATWESEN, David, G. et al.; Wells St. John P.S., 601 W. 1st Ave., Suite 1300, Spokane, WA 99201 (US).

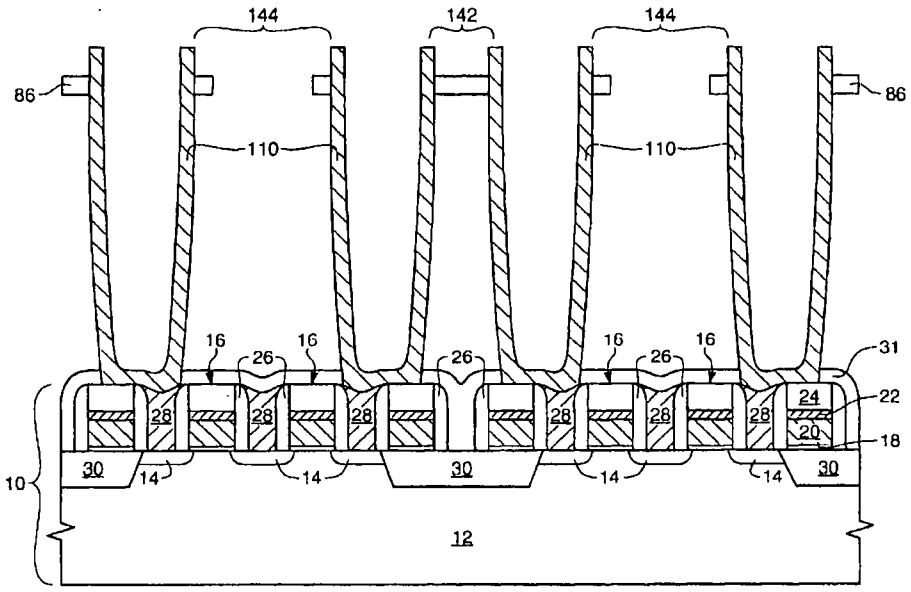
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(54) Title: SUPPORT FOR VERTICALLY-ORIENTED CAPACITORS DURING THE FORMATION OF A SEMICONDUCTOR DEVICE



(57) Abstract: A method for forming double-sided capacitors for a semiconductor device includes forming a dielectric structure (86) which supports capacitor bottom plates (110) during wafer processing. The structure is particularly useful for supporting the bottom plates during removal of a base dielectric layer (84) to expose the outside of the bottom plates to form a double-sided capacitor. The support structure further supports the bottom plates during formation of a cell dielectric layer (200), a capacitor top plate (202), and final supporting dielectric (204). An inventive structure is also described.

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